

BSS123LT1G Datasheet

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DiGi Electronics Part Number BSS123LT1G-DG

Manufacturer onsemi

Manufacturer Product Number BSS123LT1G

Description MOSFET N-CH 100V 170MA SOT23-3

Detailed Description N-Channel 100 V 170mA (Ta) 225mW (Ta) Surface M

ount SOT-23-3 (TO-236)



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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
BSS123LT1G	onsemi
Series:	Product Status:
	Active
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
100 V	170mA (Ta)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
10V	60hm @ 100mA, 10V
Vgs(th) (Max) @ Id:	Vgs (Max):
2.6V @ 1mA	±20V
Input Capacitance (Ciss) (Max) @ Vds:	FET Feature:
20 pF @ 25 V	
Power Dissipation (Max):	Operating Temperature:
225mW (Ta)	-55°C ~ 150°C (TJ)
Mounting Type:	Supplier Device Package:
Surface Mount	SOT-23-3 (TO-236)
Package / Case:	Base Product Number:
TO-236-3, SC-59, SOT-23-3	BSS123

Environmental & Export classification

8541.21.0095

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
LITCHC.	



MOSFET – Power 170 mAmps, 100 Volts

N-Channel SOT-23

BSS123LT1G, BVSS123LT1G

Features

- HBM Class 0A, MM Class M1B (Note 4)
- BVSS Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	100	Vdc
Gate–Source Voltage – Continuous – Non–repetitive ($t_p \le 50 \mu s$)	V _{GS} V _{GSM}	±20 ±40	Vdc Vpk
Drain Current - Continuous (Note 1) - Pulsed (Note 2)	I _D I _{DM}	0.17 0.68	Adc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

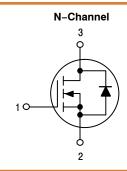
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 3) T _A = 25°C Derate above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

- The Power Dissipation of the package may result in a lower continuous drain current.
- 2. Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.
- 3. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
- ESD between the gate and source serves only, no gate overvoltage rating is implied.

170 mAMPS 100 VOLTS

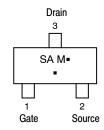
 $R_{DS(on)} = 6 \Omega$



MARKING DIAGRAM & PIN ASSIGNMENT



SOT-23 CASE 318 STYLE 21



SA = Device Code
M = Date Code
• = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

BSS123LT1G, BVSS123LT1G

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic			Min	Тур	Max	Unit
OFF CHARACTERISTICS		•		•	•	
Drain-Source Breakdown Voltage (V _{GS} = 0, I _D = 250 μAdc)		V _{(BR)DSS}	100	-	_	Vdc
Zero Gate Voltage Drain Current $(V_{GS} = 0, V_{DS} = 100 \text{ Vdc})$ $T_J = 25^{\circ}\text{C}$ $T_J = 125^{\circ}\text{C}$;	I _{DSS}	- -	- -	15 60	μAdc
Gate-Body Leakage Current (V _{GS} = 20 Vdc, V _{DS} = 0)		I _{GSS}	-	-	50	nAdc
ON CHARACTERISTICS (Note 5)		<u>.</u>		•		
Gate Threshold Voltage $(V_{DS} = V_{GS}, I_D = 1.0 \text{ mAdc})$		V _{GS(th)}	1.6	-	2.6	Vdc
Static Drain–Source On–Resistance ($V_{GS} = 10 \text{ Vdc}$, $I_D = 100 \text{ mAdc}$)		r _{DS(on)}	-	-	6.0	Ω
Forward Transconductance (V _{DS} = 25 Vdc, I _D = 100 mAdc)	9 _{fs}	80	-	-	mmhos	
DYNAMIC CHARACTERISTICS		<u>.</u>		•		
Input Capacitance (V _{DS} = 25 Vdc, V _{GS} = 0, f = 1.0 MHz)		C _{iss}	-	20	-	pF
Output Capacitance (V _{DS} = 25 Vdc, V _{GS} = 0, f = 1.0 MHz)		C _{oss}	-	9.0	-	pF
Reverse Transfer Capacitance $(V_{DS} = 25 \text{ Vdc}, V_{GS} = 0, f = 1.0 \text{ MHz})$		C _{rss}	-	4.0	-	pF
SWITCHING CHARACTERISTICS(4)		-		•	•	•
Turn-On Delay Time	(V _{CC} = 30 Vdc, I _C = 0.28 Adc,	t _{d(on)}	_	20	-	ns
Turn-Off Delay Time	V_{GS} = 10 Vdc, R_{GS} = 50 Ω)	t _{d(off)}	-	40	-	ns
REVERSE DIODE						
Diode Forward On-Voltage (I _D = 0.34 Adc, V _{GS} = 0 Vdc)		V _{SD}	-	-	1.3	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ORDERING INFORMATION

Device	Package	Shipping [†]
BSS123LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
BVSS123LT1G*	SOT-23 (Pb-Free)	3,000 / Tape & Reel
BSS123LT7G	SOT-23 (Pb-Free)	3,500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*BVSS Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP

^{5.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

Capable.

BSS123LT1G, BVSS123LT1G

TYPICAL ELECTRICAL CHARACTERISTICS

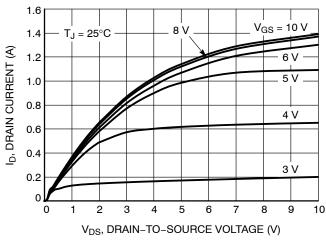


Figure 1. On-Region Characteristics

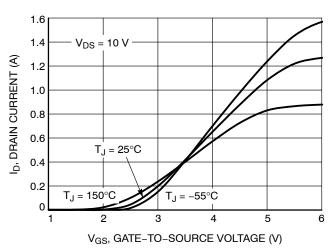


Figure 2. Transfer Characteristics

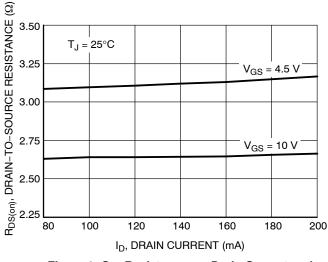


Figure 3. On–Resistance vs. Drain Current and Gate Voltage

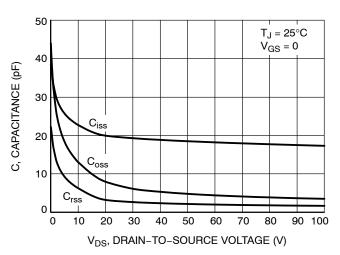


Figure 4. Capacitance Variation

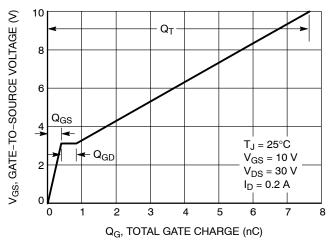


Figure 5. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

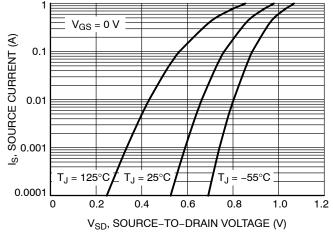


Figure 6. Diode Forward Voltage vs. Current

BSS123LT1G, BVSS123LT1G

TYPICAL ELECTRICAL CHARACTERISTICS

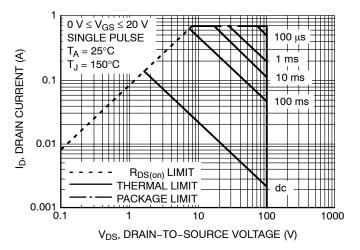


Figure 7. Maximum Rated Forward Biased Safe Operating Area

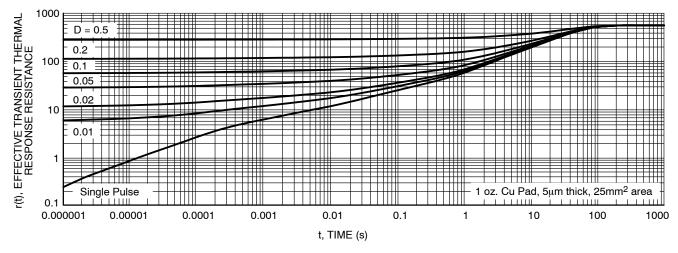


Figure 8. Thermal Response



MECHANICAL CASE OUTLINE

MILLIMETERS

MIN

0.89

0.01

0.37

0.08

2.80

1.20

1.78

0.30

0.35

2.10

O°

NOM

1.00

0.06

0.44

0.14

2.90

1.30

1.90

0.43

0.54

2.40

PACKAGE DIMENSIONS



SOT-23 (TO-236) 2.90x1.30x1.00 1.90P **CASE 318 ISSUE AU**

DATE 14 AUG 2024

MAX

1.11

0.10

0.50

0.20

3.04

1.40

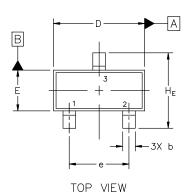
2.04

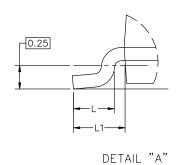
0.55

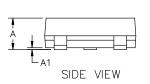
0.69

2.64

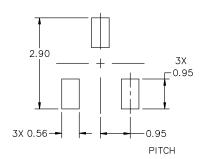
10°











Scale 3:1

NOTES:

DIM

Α

Α1

b

С

D

Ε

е L

L1

HE

Τ

- DIMENSIONING AND TOLERANCING 1.
- PER ASME Y14.5M, 2018. CONTROLLING DIMENSIONS: MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE
- BASE MATERIAL.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

= Date Code

= Pb-Free Package

RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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^{*}This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.

SOT-23 (TO-236) 2.90x1.30x1.00 1.90P CASE 318 ISSUE AU

DATE 14 AUG 2024

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	ı	
STYLE 9:	STYLE 10:	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN		PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE		2. CATHODE	2. DRAIN	2. GATE
3. CATHODE	3. GATE		3. ANODE	3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODE	3. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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